

General Description

The HSP10P20 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

The HSP10P20 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

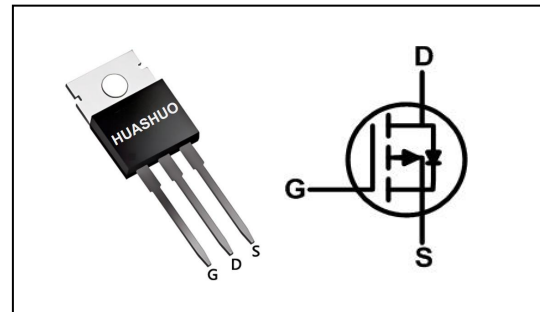
Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench Technology

Product Summary

V_{DS}	-200	V
$R_{DS(ON),typ}$	650	m Ω
I_D	-10	A

TO-220 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-200	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-10	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-7.5	A
I_{DM}	Pulsed Drain Current ²	-40	A
EAS	Single Pulse Avalanche Energy ³	81	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	80	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.6	$^\circ C/W$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-200	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-3A$	---	650	810	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-2	-2.9	-4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-200V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-10V$, $I_D=-3A$	---	5.5	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	5.4	---	Ω
Q_g	Total Gate Charge	$V_{DS}=-50V$, $V_{GS}=-10V$, $I_D=-3A$	---	82	---	nC
Q_{gs}	Gate-Source Charge		---	19	---	
Q_{gd}	Gate-Drain Charge		---	22	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-50V$, $V_{GS}=-10V$, $R_G=3.3\Omega$, $I_D=-3A$	---	18	---	ns
T_r	Rise Time		---	4.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	49.5	---	
T_f	Fall Time		---	28	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2155	---	pF
C_{oss}	Output Capacitance		---	49	---	
C_{rss}	Reverse Transfer Capacitance		---	39	---	

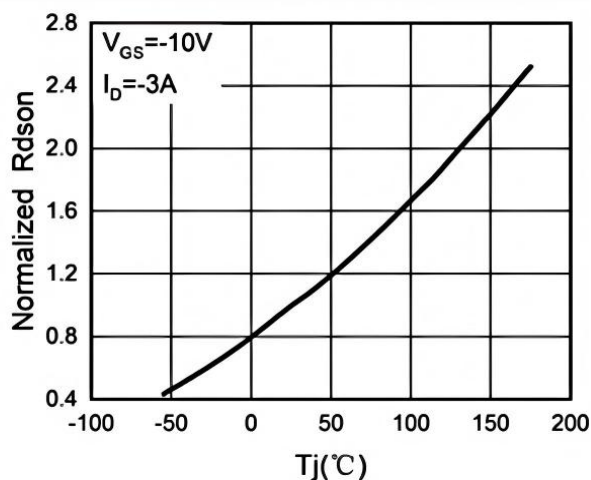
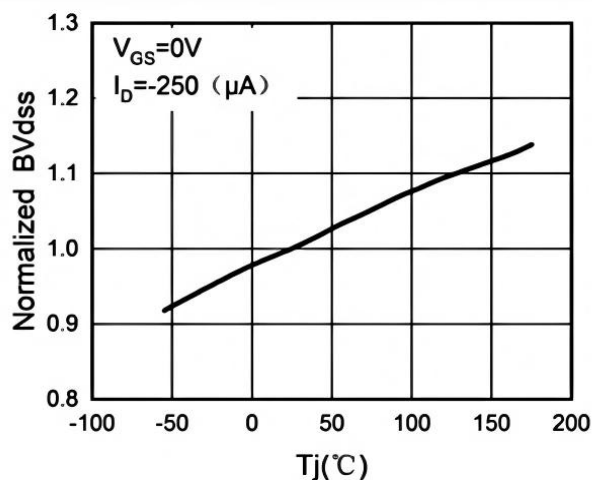
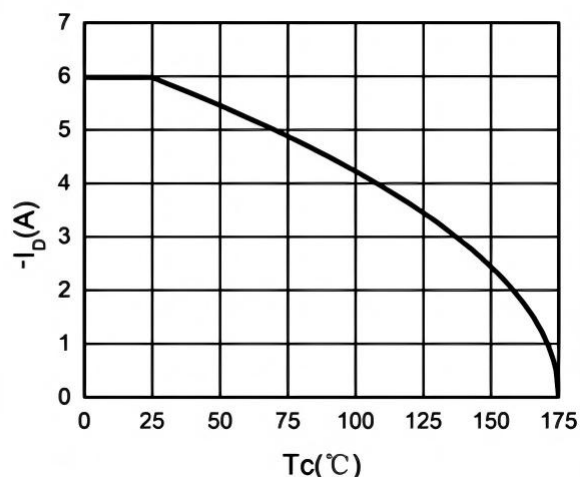
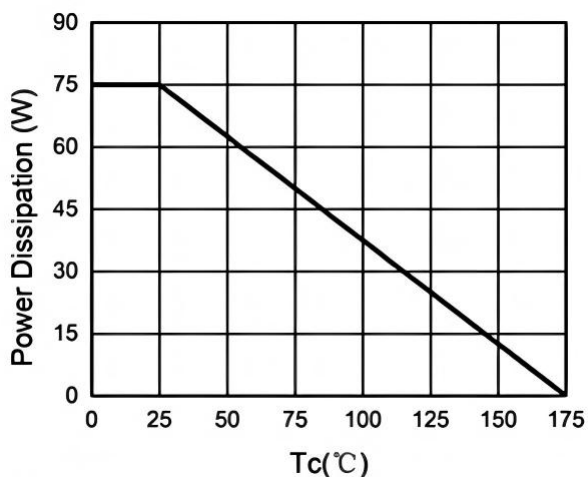
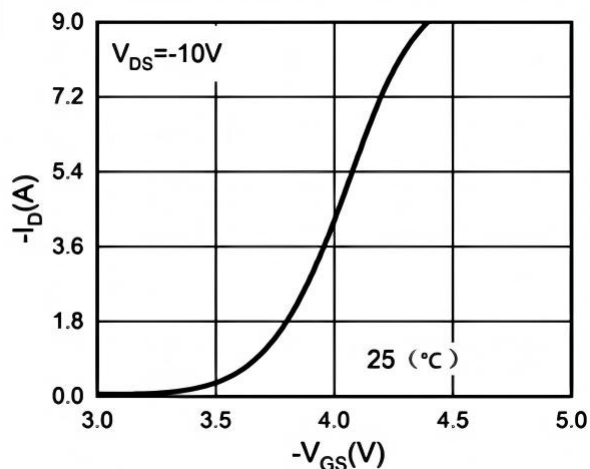
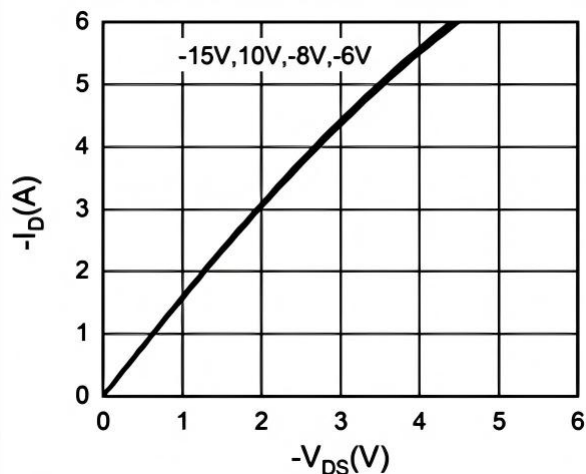
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-10	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-3A$, $dI/dt=-100A/\mu s$, $T_J=25^\circ\text{C}$	---	63	---	nS
Q_{rr}	Reverse Recovery Charge		---	195	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics





P-Ch 200V Fast Switching MOSFETs

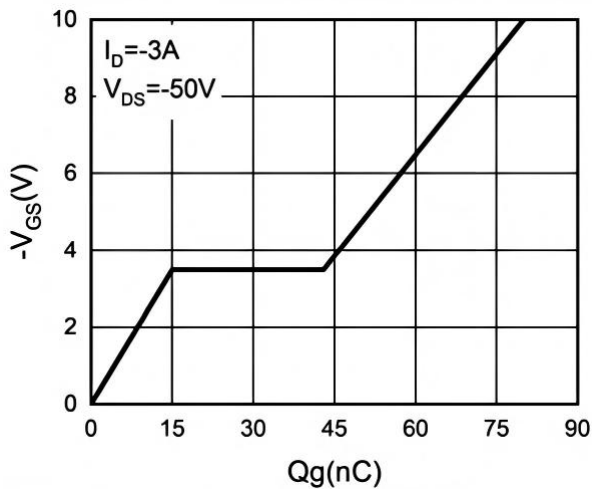


Fig.7 Gate Charge Waveforms

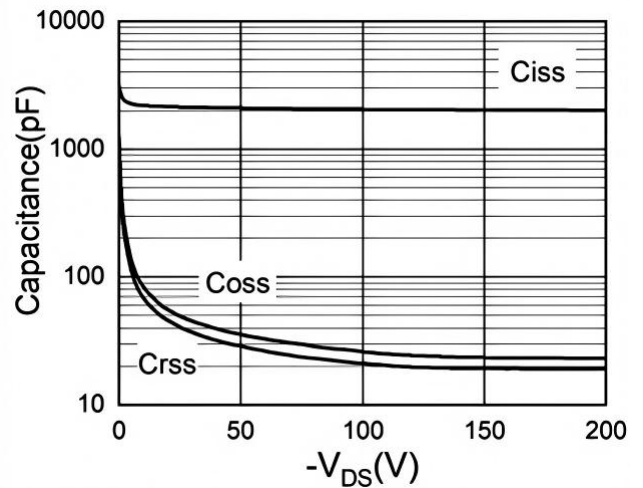


Fig.8 Capacitance

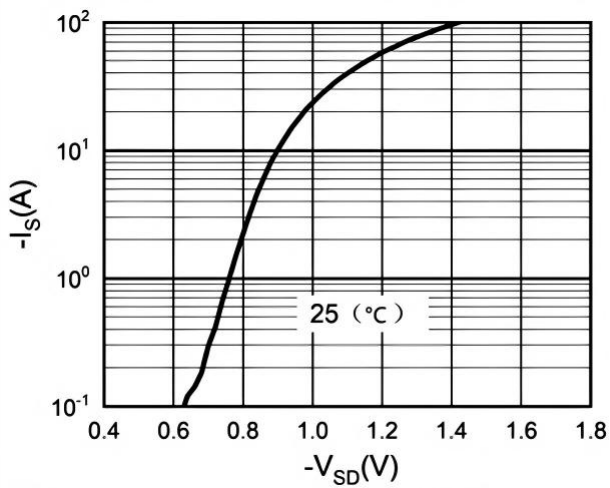


Fig.9 Body Diode Characteristics

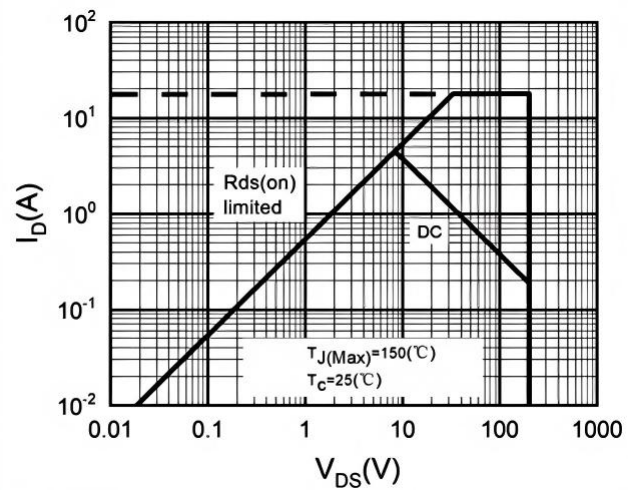
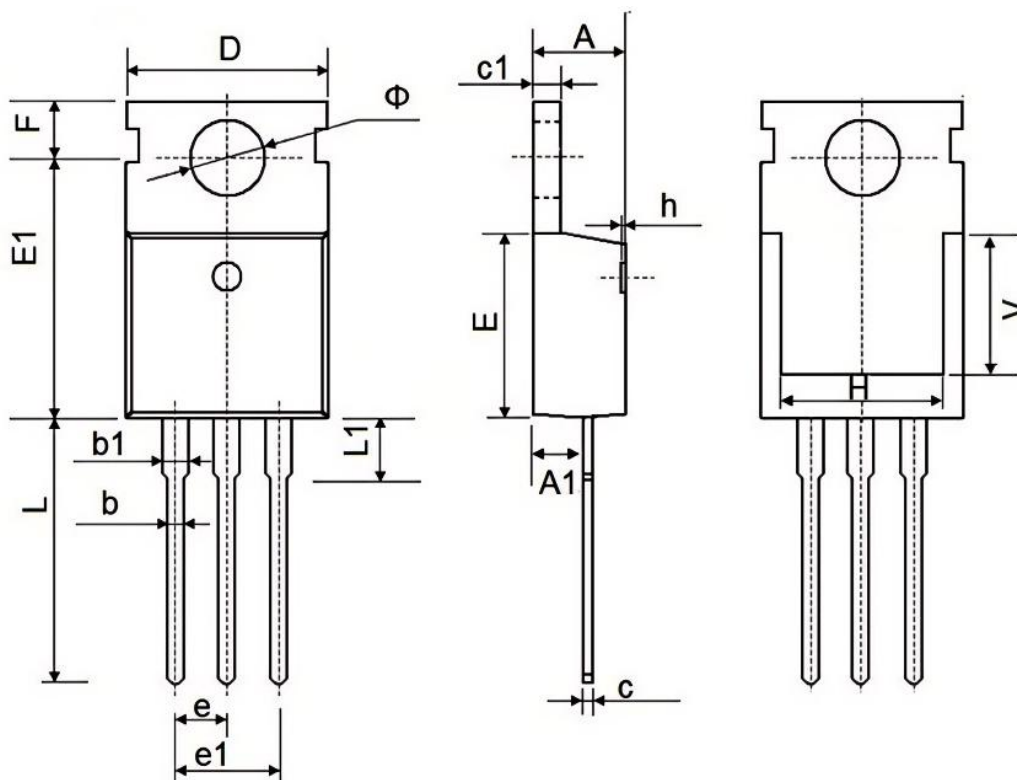


Fig.10 Maximum Safe Operating Area

Ordering Information

Part Number	Package code	Packaging
HSP10P20	TO-220	1000/Box

TO-220 Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	2.200	2.600	0.087	0.102
b	0.700	0.950	0.028	0.037
b1	1.170	1.410	0.046	0.056
C	0.450	0.650	0.018	0.026
c1	1.200	1.400	0.047	0.055
D	9.600	10.400	0.378	0.409
E	8.8500	9.750	0.348	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.750	14.300	0.502	0.563
L1	2.850	3.950	0.112	0.156
V	7.500 REF.		0.295 REF.	
Φ	3.400	4.000	0.134	0.157

HSP10P20 Marking:

